



DESCRIPTION

The AM065NS10L is available in TO-220 and TO-263 Packages.

BV _{DSS}	R _{DS(ON)}	I _D
100V	6mΩ	80A

APPLICATION

- Synchronous rectification
- High speed switching applications

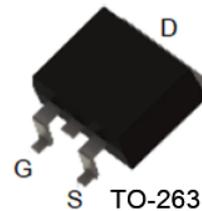
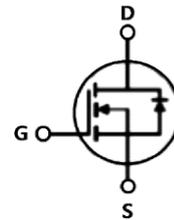
ORDERING INFORMATION

Package Type	Part Number	
TO-220 SPQ:50pcs/Tube	T3	AM065NS10LT3U
		AM065NS10LT3VU
TO-263 SPQ:800pcs /Reel	S2	AM065NS10LSR
		AM065NS10LSVR
Note	V: Halogen free Package R: Tape & Reel	
AiT provides all RoHS products		

FEATURE

- Fast Switching
- R_{DS(ON)typ.}=6mΩ @ V_{GS}=10V
- Low On-Resistance
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness

PIN DESCRIPTION



Pin#		Symbol	Function
TO-220	TO-263		
1	1	G	Gate
2	2,4	D	Drain
3	3	S	Source

**ABSOLUTE MAXIMUM RATINGS**T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	100	V
Continuous Drain Current, Silicon Limited	I _D	96	A
Continuous Drain Current, Package Limited		80	A
Continuous Drain Current @T _C =100°C, Silicon Limited		60.7	A
Pulsed Drain Current	I _{DM} ⁽¹⁾	320	A
Gate-Source Voltage	V _{GS}	±20	V
Avalanche Energy	E _{AS} ⁽²⁾	225	mJ
Power Dissipation	P _D	125	W
Derating Factor above 25°C		1	W/°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	150 , -55 to 150	°C
Maximum Temperature for Soldering	T _L	260	°C
THERMAL RESISTANCE			
Thermal Resistance, Junction-Case	R _{θJC}	1	°C/W
Thermal Resistance, Junction-Ambient	R _{θJA}	62.5	

(1) Repetitive Rating : Pulse width limited by maximum junction temperature

(2) L=0.5mH, I_{as}=30A, Start T_J=25°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V _{DSS}	V _{GS} =0V, I _D =250μA	100	110	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =80V, V _{GS} =0V @T _C =125°C	-	-	100	μA
Gate-Source Forward Leakage	I _{GSS(F)}	V _{GS} =+20V	-	-	100	nA
Gate-Source Reverse Leakage	I _{GSS(R)}	V _{GS} =-20V	-	-	-100	nA
ON CHARACTERISTICS						
Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =35A	-	8.2	9.5	mΩ
		V _{GS} =10V, I _D =50A	-	6	6.5	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1	1.8	2.5	V
Dynamic CHARACTERISTICS						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0, f=1MHz	-	3670	-	pF
Output Capacitance	C _{oss}		-	780	-	
Reverse Transfer Capacitance	C _{rss}		-	12	-	
Total Gate Charge	Q _g	V _{DD} =50V, I _D =50A, V _{GS} =10V	-	65	-	nC
Gate-Source charge	Q _{gs}		-	13	-	
Gate-Drain charge	Q _{gd}		-	11	-	
Gate resistance	R _G	V _{GS} =0, V _{DS} =0	-	1.2	-	Ω
Switching CHARACTERISTICS						
Turn-on Delay Time	t _{d(ON)}	V _{DD} =50V, I _D =50A, V _{GS} =10V, R _G =3Ω, Resistive Load	-	17	-	nS
Rise Time	t _r		-	36	-	
Turn-Off Delay Time	t _{d(OFF)}		-	40	-	
Fall Time	t _f		-	24	-	
Source-Drain Diode CHARACTERISTICS						
Continuous Source Current	I _S		-	-	60	A
Maximum Pulsed Current	I _{SM}		-	-	320	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =50A	-	-	1.2	V
Reverse Recovery Time	t _{rr}	I _S =20A, V _{GS} =0, di/dt=100A/us	-	65	-	ns
Reverse Recovery Charge	Q _{rr}		-	120	-	nC

* Pulse width t_p≤300μs, δ≤2%.



TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Safe Operating Area

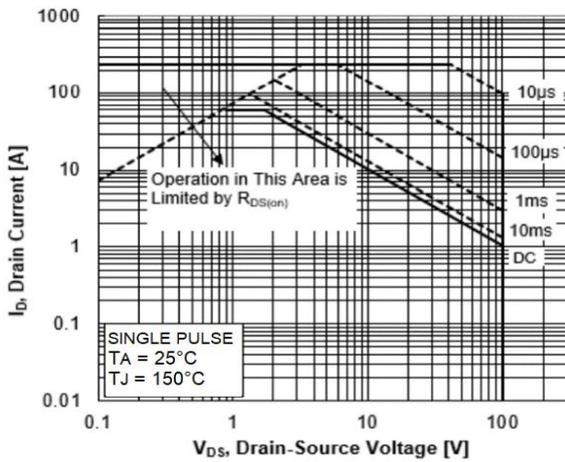


Fig 2. Maximum Power Dissipation Vs Case Temperature

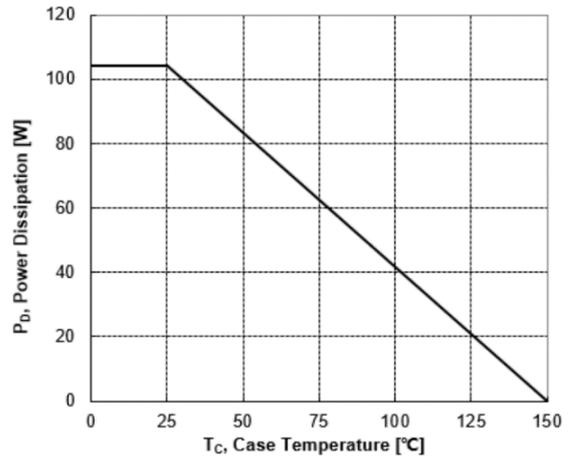


Fig 3. Maximum Continuous Drain Current Vs Case Temperature

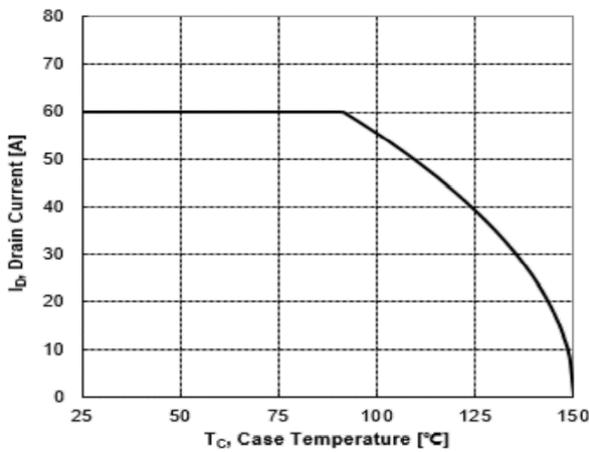


Fig 4. Typical Output Characteristics

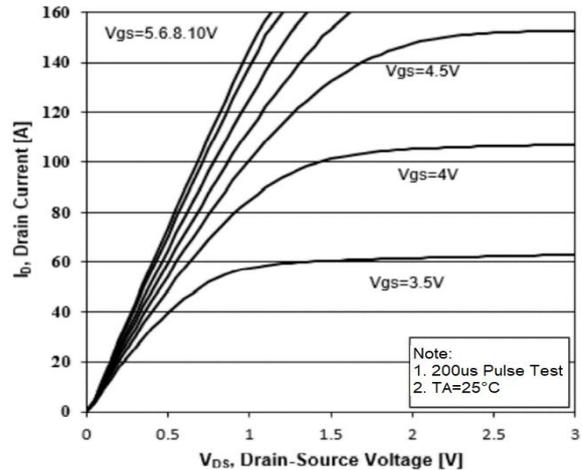


Fig 5. Transient Thermal Impedance

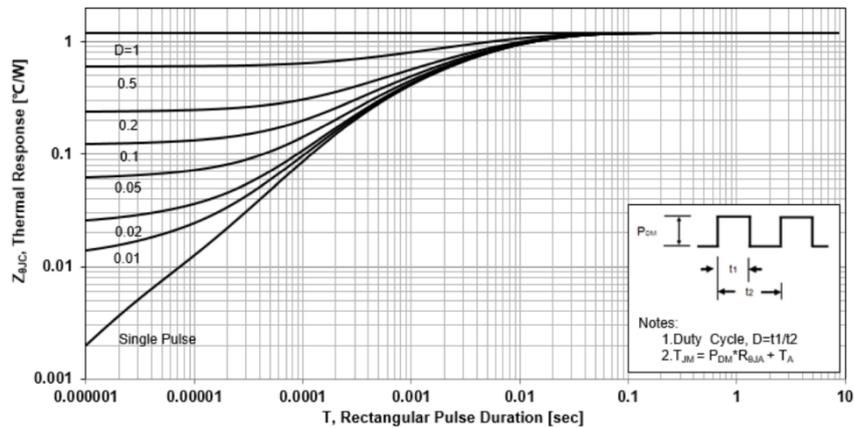




Fig 6. Typical Transfer Characteristics

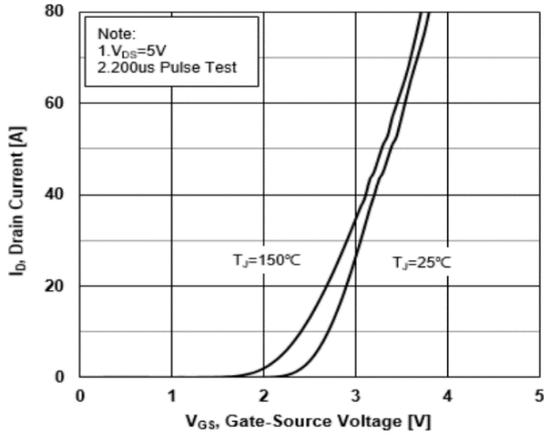


Fig 7. Source-Drain Diode Forward Characteristics

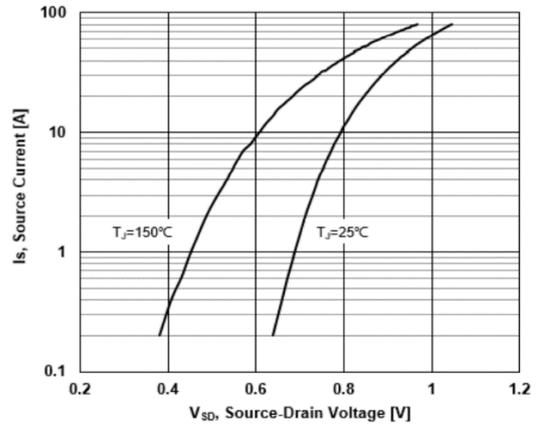


Fig 8. Drain-Source On-Resistance vs Drain Current

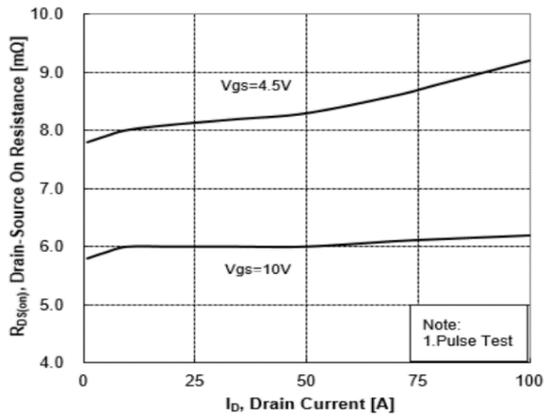


Fig 9. Normalized On-Resistance vs Junction Temperature

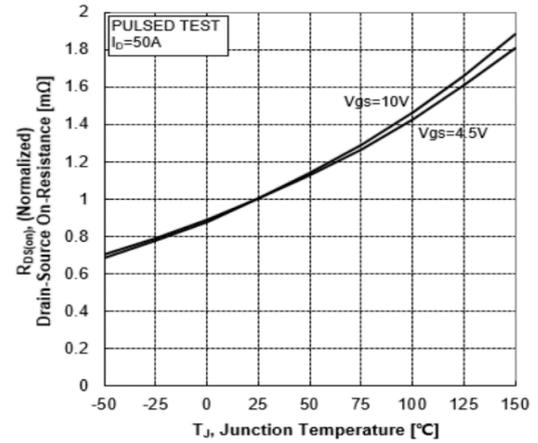


Fig 10. Normalized Threshold Voltage vs Junction Temperature

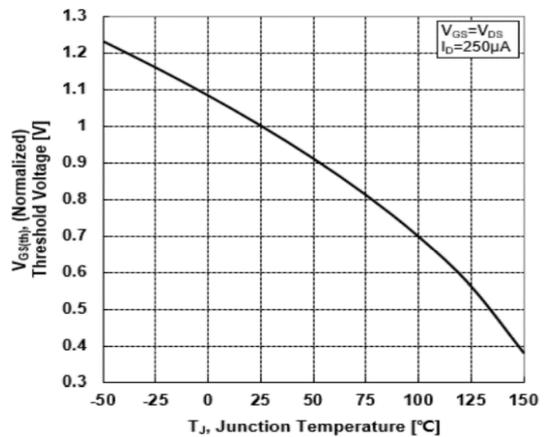


Fig 11. Normalized Breakdown Voltage vs Junction Temperature

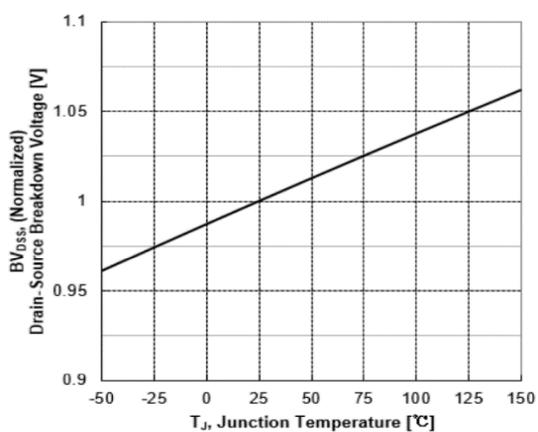




Fig12. Capacitance Characteristics

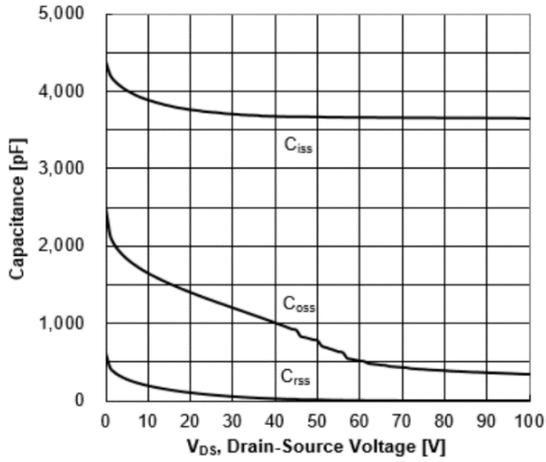


Fig 13. Typical Gate Charge vs Gate-Source Voltage

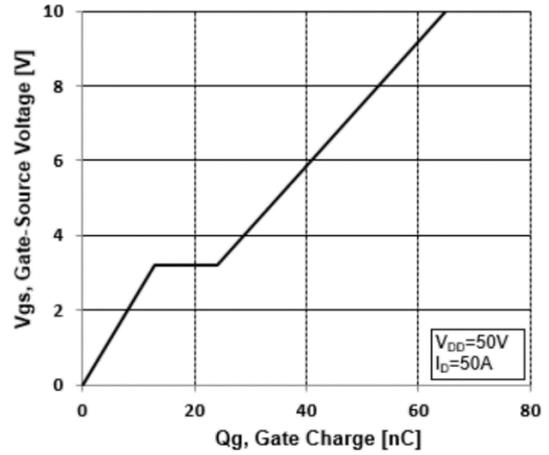


Fig 14. Resistive Switching Test Circuit

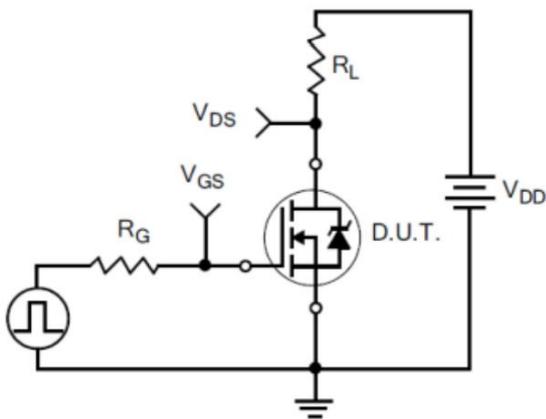


Fig 15. Resistive Switching Waveforms

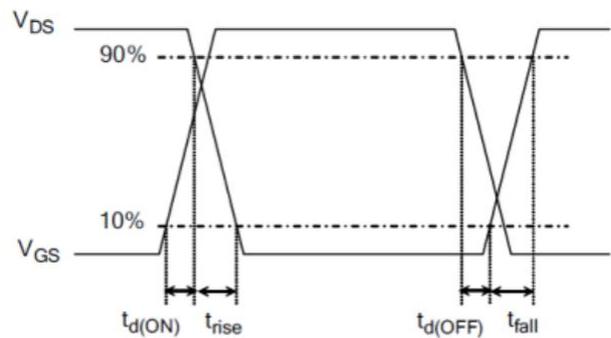


Fig 16. Gate Charge Test Circuit

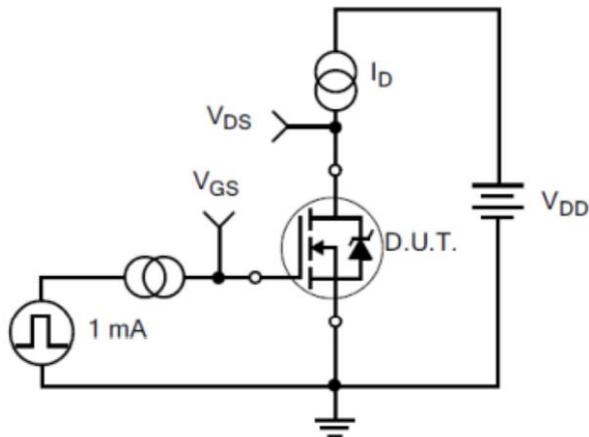


Fig 17. Gate Charge Waveforms

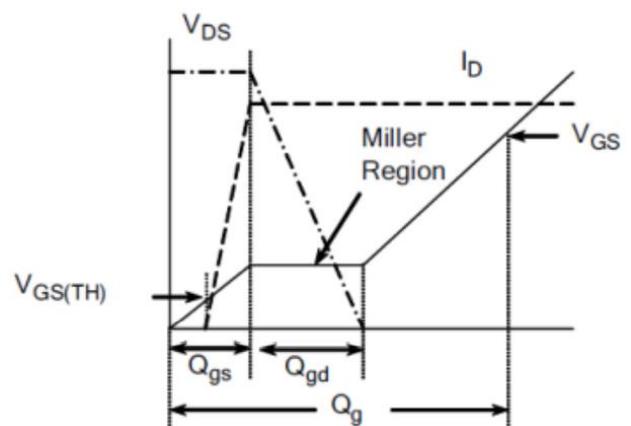




Fig 18. Diode Reverse Recovery Test Circuit

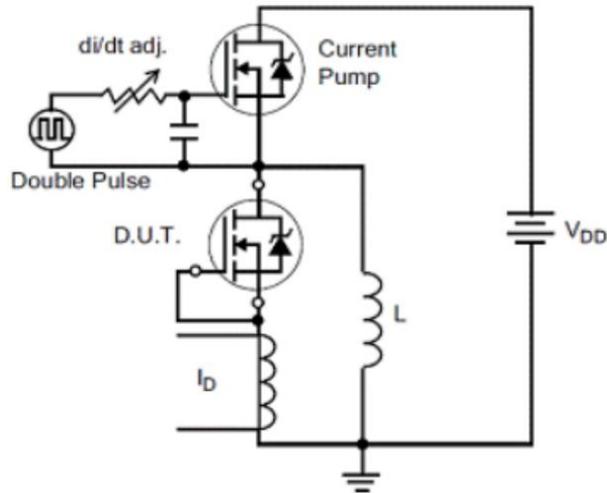


Fig 19. Diode Reverse Recovery Waveform

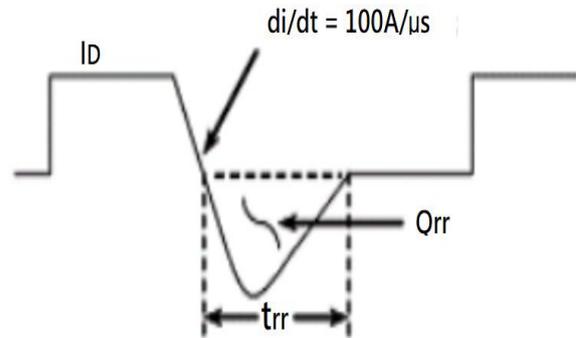


Fig 20. Unclamped Inductive Switching Test Circuit

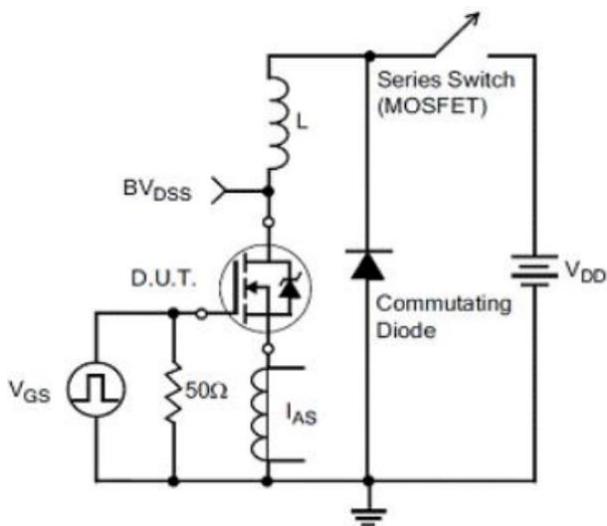
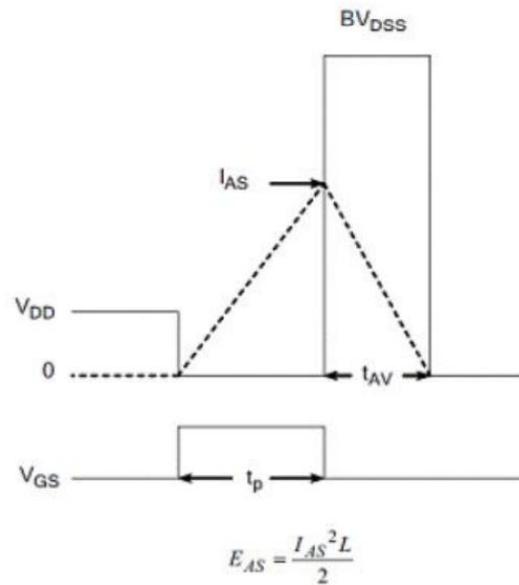


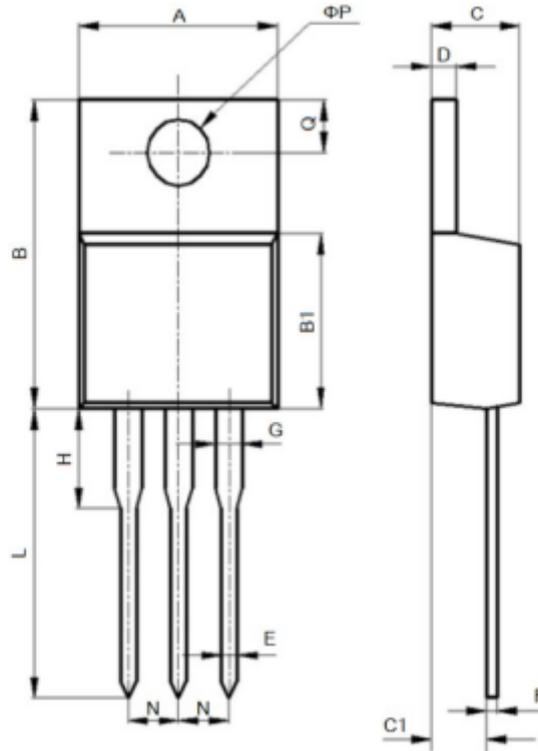
Fig 21. Unclamped Inductive Switching Waveform





PACKAGE INFORMATION

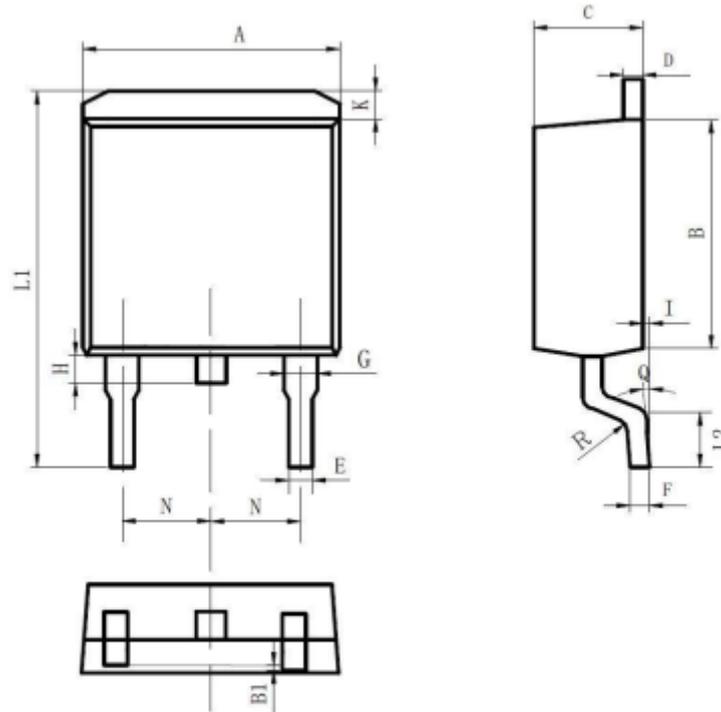
Dimension in TO-220 (Unit: mm)



Symbol	Min.	Max.
A	9.600	10.600
B	15.000	16.000
B1	8.900	9.500
C	4.300	4.800
C1	2.300	3.100
D	1.200	1.400
E	0.700	0.900
F	0.300	0.600
G	1.170	1.370
H	2.700	3.800
L	12.600	14.800
N	2.340	2.740
Q	2.400	3.000
ΦP	3.500	3.900



Dimension in TO-263 (Unit: mm)



Symbol	Min.	Max.
A	9.800	10.400
B	8.900	9.500
B1	0.000	0.100
C	4.400	4.800
D	1.160	1.370
E	0.700	0.950
F	0.300	0.600
G	1.070	1.470
H	1.300	1.800
K	0.950	1.370
L1	14.500	16.500
L2	1.600	2.300
I	0.000	0.200
Q	0°	8°
R	0.4°	
N	2.390	2.690



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